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**APPLICANT**

ASANO ET AL.

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## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

	Supplementary EP Search Report mailed October 15, 2008 in corresponding EP Application 04726292.8
	Agarwal et al, "700-V Asymmetrical 4H-SiC Gate Turn-Off Thyristors (GTO's), IEEE Electron Device Letters, Vol. 18, No. 11, November 1997, pp. 518-520
	Agarwal et al, "Dynamic Performance of 3.1 kV 4H-SiC Asymmetrical GTO Thyristors", Materials Science Forum, 389-393, 2002, pp. 1349-1352
	Ryu et al, "3100 V, Asymmetrical, Gate Turn-Off (GTO) Thyristors in 4H-SiC", IEEE Electron Device Letters, vol. 22, no. 3, March 2001, pp.127-129

\*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)